

assume 
$$gm_1 = gm_2$$
  
 $gm_{3,4} = -0.75$  gms, 6

$$r=0$$
assume  $gm_1=gm_2$ 
 $gm_3=gm_4$ 

 $=4kTr\left(\frac{2}{gm_1}+\frac{3.5gms}{gm_1^2}\right)$ 

$$V_{n,out^{2}} = I_{n,out^{2}} \cdot Rout^{2}$$

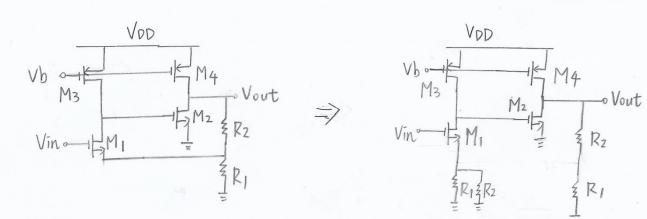
$$= 4KTY (gm_{1} + gm_{2} + gm_{3} + gm_{4}) \cdot Rout^{2}$$

$$= 4KTY (2gm_{1} + 2gm_{3}) \cdot Rout^{2}$$

$$= V_{n,out^{2}} = V_{n,out^{2}} - 4KTY (2gm_{1} + 2gm_{3}) \cdot Rout^{2}$$

$$V_{n, \bar{1}n^{2}} = \frac{V_{m, out^{2}}}{AV^{2}} = \frac{4kTV (2gm_{1} + 2gm_{3}) \cdot Rout^{2}}{gm_{1}^{2} \cdot Rout^{2}}$$

$$= 4kTV \left(\frac{2}{gm_{1}} + \frac{2gm_{3}}{gm_{1}^{2}}\right)$$



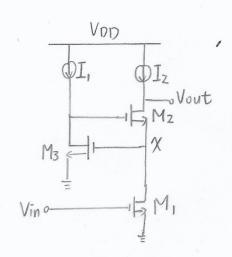
$$V_{DD}$$
 $V_{DD}$ 
 $V_{M_3}$ 
 $M_2$ 
 $M_2$ 
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 $M_4$ 

Av, open loop = 
$$\frac{gm_1 ro_3}{1+gm_1 (R_1/1/R_2)}$$
.  $gm_2$ .  $[ro_2// ro_4// (R_2+R_1)]$ 

Rout, open = Y04// Y02// (Rz+R1)

$$\beta = \frac{R_1}{R_1 + R_2}$$

$$AV, CL = \frac{AV, Open loop}{1+ BA}$$



$$I_1 = \frac{1}{2} \left( \frac{w}{L} \right)_3 \left( Vgs_3 - Vtn_3 \right)^2 NnCox$$

$$I_2 = \frac{1}{z} \left( \frac{w}{L} \right)_2 \left( Vg s_2 - Vt n_2 \right)^2 \mu_n Cox$$

$$Vg_2 = \sqrt{\frac{2I_2}{\left(\frac{W}{L}\right)_2 \mu n Co X}} + Vtn_2 + VX = 1.3V$$

(h)

Assume I, & Iz are ideal current source

Rout, OL= gmz rozro,

The purpose of using  $C_c$  is move the interstage pole toward the origin (from  $\frac{1}{(VO4/(VOZ))Cparasitic}$  to  $\frac{1}{(VO4/(VOZ))(VO6/(VOT))gmbCc}$ ) and push the second stage pole away from dominant pole and origin (from  $\frac{1}{(VOL/(VOT))CL}$  to  $\frac{gmb}{C_L}$ ), but  $C_c$  will bring the disadvantage about having a RHP zero  $\frac{gmb}{C_c}$  cause unstable

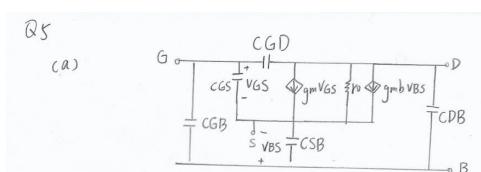
(b)

"MI Mb

Re Cc

M7

To add a resistor Rc to move the zero from  $\frac{gmb}{Cc}$  (RHP) to  $\frac{1}{Cc}(\frac{1}{gmb}-Rc)$  if  $\frac{1}{gmb} \le Rc$ , then the zero will move to LHP



- (b)
  1. Channel length modulation
  - The actual length of the channel gradually decreases as the potential difference between the gate and the drain decreases. When mos at saturation region, the length of Leff decreases, and the current increases.

n Most small signal model

Leff Leff Leff 
$$L$$
 Leff  $L$  Leff  $L$  Left  $L$  L

- => For design, when ID is at saturation region, the VDS increases or decreases will change ro, and this phenomenon brings nonlinearity.
- 2. Body effect
- => For nMosT, if VB <0, more holes are attracted to the substrate connection, leaving negative charge under the gate. Thus, we need higher gate voltage to build the inverse channel.
- => For design, when  $VBS \neq 0$ , then  $Vth = Vtho + V(Jz\phi f VBS Jz\phi f)$ , the coefficient will appear to change ID.

